

Silicon NPN Power Transistors

2SD1430

DESCRIPTION

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- With TO-3PH package
- High voltage ,high speed
- Low collector saturation voltage

APPLICATIONS

- Designed for use in color TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

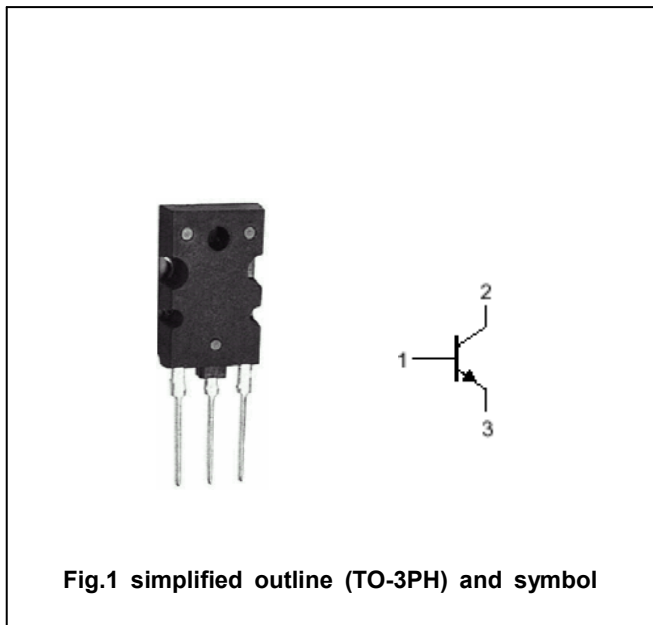


Fig.1 simplified outline (TO-3PH) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	600	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		3.5	A
I <sub>E</sub>	Emitter current		-3.5	A
P <sub>D</sub>	Total power dissipation	T <sub>C</sub> =25°C	80	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =0.8A		4.0	8.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =0.8A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =500V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.5A; V <sub>CE</sub> =5V	8	20		
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A; V <sub>CE</sub> =10V		3		MHz
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V; f=1.0MHz		95		pF
t <sub>f</sub>	Fall time	I <sub>C</sub> =3A; I <sub>B1</sub> =0.8A			1.0	μs

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PACKAGE OUTLINE

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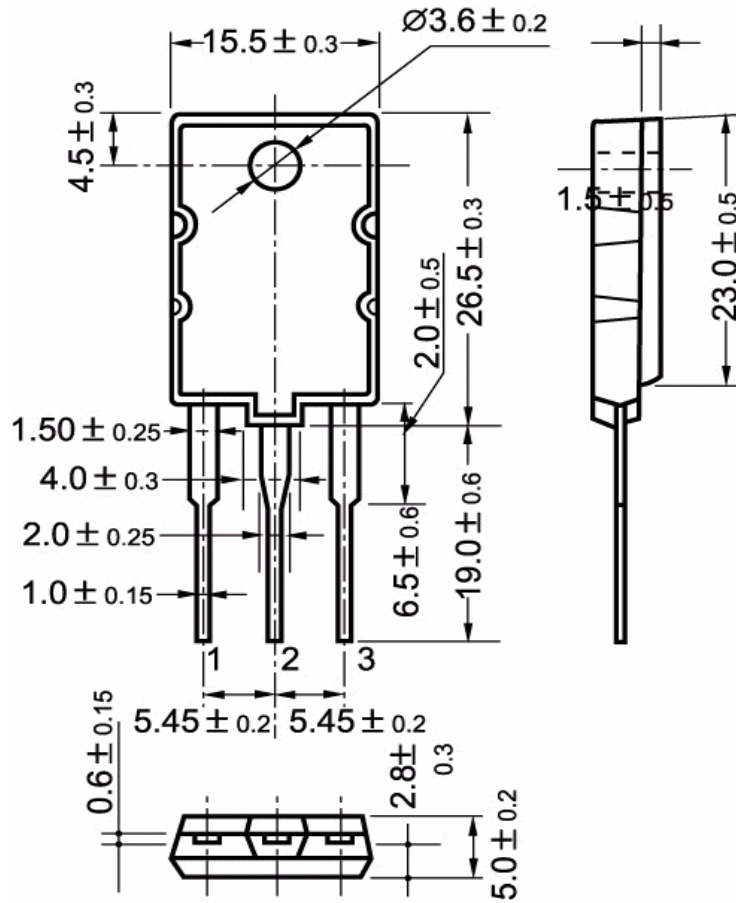


Fig.2 outline dimensions